

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MMDT5551

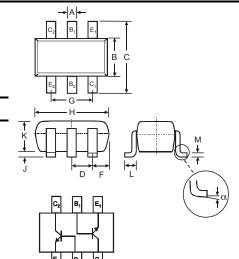
DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (MMDT5401)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: K4N, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



SOT-363										
Dim	Min	Max								
Α	0.10	0.30								
В	1.15	1.35								
С	2.00	2.20								
D	0.65 N	ominal								
F	0.30	0.40								
Н	1.80	2.20								
J	_	0.10								
K	0.90	1.00								
L	0.25	0.40								
М	0.10	0.25								
α	0°	8°								
All Din	nensions	in mm								

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Collector-Base Voltage		V _{CBO}	180	V
Collector-Emitter Voltage		V_{CEO}	160	V
Emitter-Base Voltage		V_{EBO}	6.0	V
Collector Current - Continuous	(Note 1)	Ic	200	mA
Power Dissipation	(Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Notes:

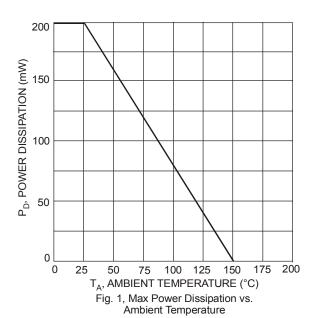
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Maximum combined dissipation.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

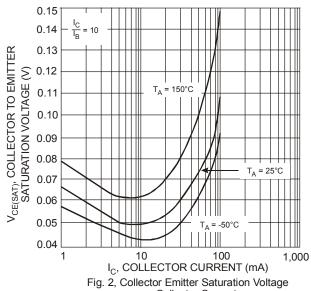


Electrical Characteristics @T_A = 25°C unless otherwise specified

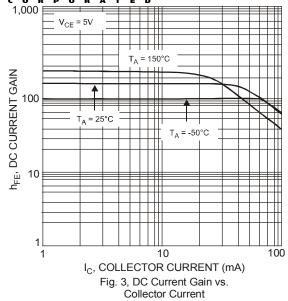
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160	_	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	_	V	$I_E = 10 \mu A, I_C = 0$
Collector Cutoff Current	Ісво	_	50	nA μA	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	_	50	nA	$V_{EB} = 4.0V, I_C = 0$
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h _{FE}	80 80 30	250 —	_	I_C = 1.0mA, V_{CE} = 5.0V I_C = 10mA, V_{CE} = 5.0V I_C = 50mA, V_{CE} = 5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.15 0.20	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage		_	1.0	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	_	6.0	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	50	250	_	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz
Noise Figure	NF	_	8.0	dB	V_{CE} = 5.0V, I_{C} = 200μA, R_{S} = 1.0kΩ, f = 1.0kHz

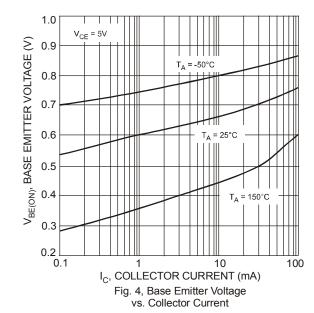
Notes: 6. Short duration pulse test used to minimize self-heating effect.

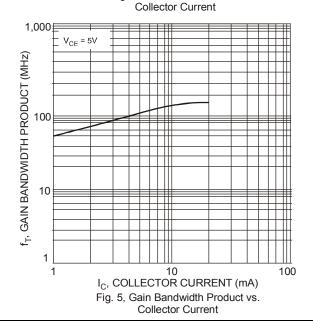










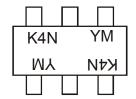


Ordering Information (Note 7)

ĺ	Device	Packaging	Shipping		
	MMDT5551-7-F	SOT-363	3000/Tape & Reel		

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K4N = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Dute Code Ney															
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Χ	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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